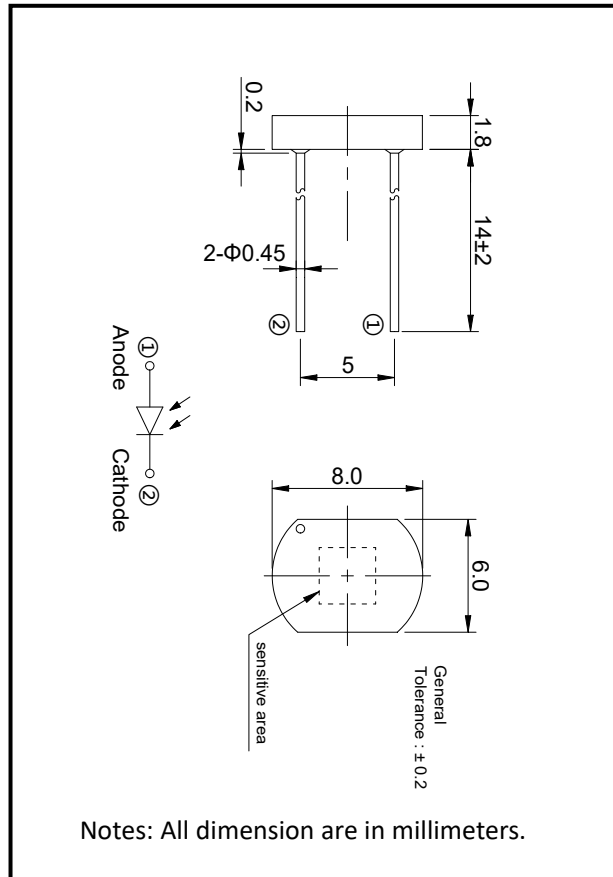
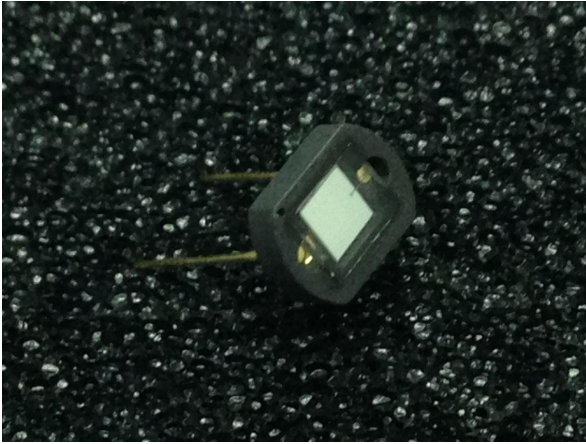


Selective wavelength photodiode

OSD9-88C



Description

The OSD9-88C is 800-900nm response high-output, high-speed silicon photo diode which is mounted in 2PIN ceramic package, permits wide angular response.

Applications

*Laser detect * Instrument equipment

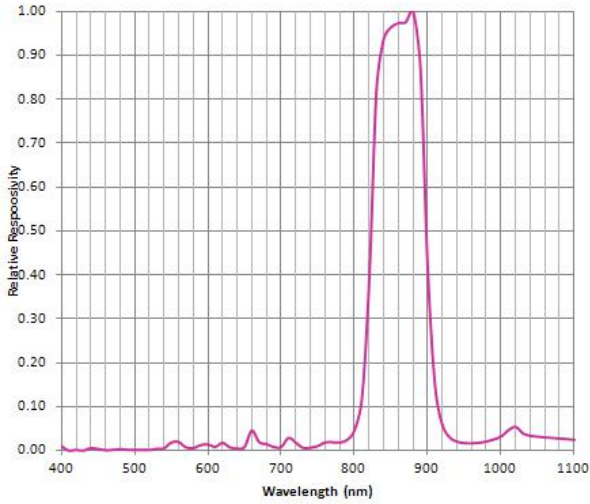
Absolute Maximum Ratings (Ta=23°C)



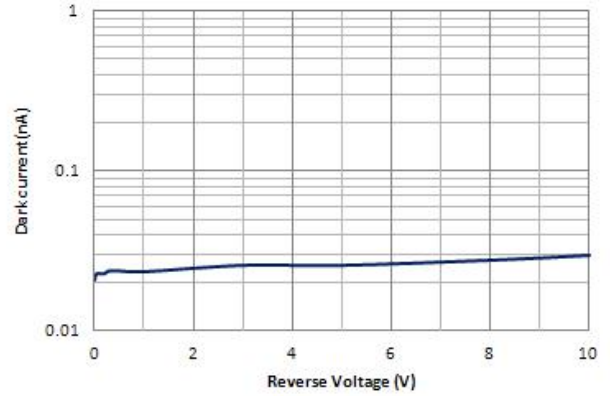
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Chip size	size	-		3.17*3.17		mm ²
Active area	A	-		2.84*2.84		mm ²
Dark current	I _D	V _R =10mV		21		pA
		V _R =10V		30		
Rise time	t _R	V _R =0V; λ =850nm; R _L =50Ω		300		ns
Tempcoeffi-cient of I _D	T _{CID}			0.18		times/°C
Reverse breakdown voltage	V _{(BR)R}	I _R =100uA E _v =0mw/cm ²	33			V
Junction Capacitance	C _J	V _R =0V f=1MHz E _e =0mW/cm ²		69		pF
		V _R =5V f=1MHz E _e =0mW/cm ²		21		
Photo sensitivity	S _R	880nm		0.55		A/W
Spectral Application Range	λ range		780		900	nm
Spectral Response-Peak	λ _p			880		nm
Shunt resistance	R _{sh}	V _R =10mV		0.5		GΩ
Angular Resp 50% Resp Pt	θ ^{1/2}			±20		Degrees



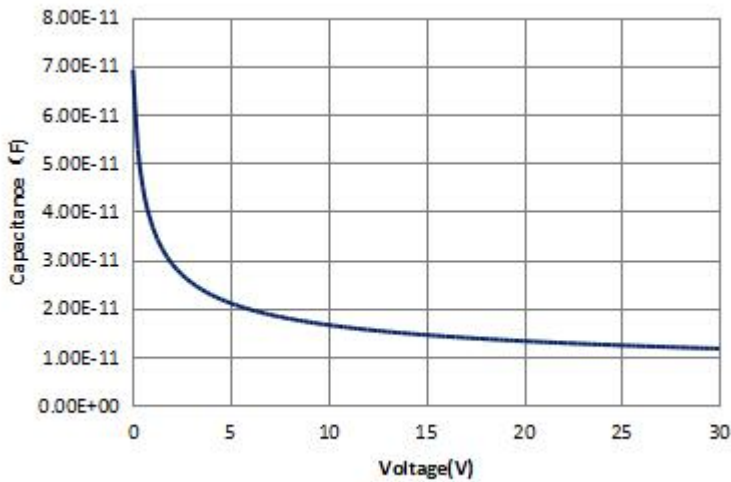
SPECTRAL RESPONSE (Ta=23°C)



DARK CURRENT VS. REVERSE VOLTAGE (Ta=23°C)



CAPACITANCE VS. REVERSE VOLTAGE (Ta=23°C)



Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject change without notice.

OTRON ELECTRONIC TECHNOLOGY CO.LTD

TEL:+86-21-54971821

FAX:+86-21-54971823

EMAIL:frank.shuai@e-otron.com

<http://www.e-otron.com>